WSD13N10TDN33

Dual N-Channel MOSFET

General Description

The WSD13N10TDN33 uses advanced technology to provide excellent $R_{DS(ON)}$, low gate charge and operation with gate voltages as low as 4.5V.

This device is suitable for use as a Battery protection or in other Switching application.

Product Summery

BV_{DSS}	$R_{DS(ON)}$	I_D
100V	70mΩ	15A

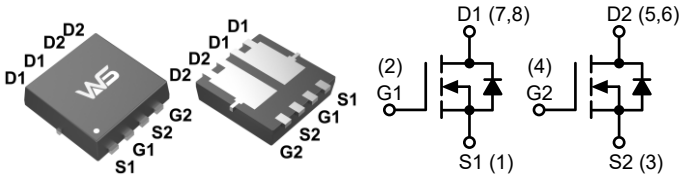
Features

- 100% UIS + R_g Tested.
- Reliable and Rugged
- Lead Free and Green Devices Available (RoHS Compliant)
- Moisture Sensitivity Level MSL1 (per JEDEC J-STD-020D)

Applications

- Power Management in Notebook Computer, Portable Equipment and Battery Powered Systems.

DFN3X3-8L Pin Configuration



Absolute Maximum Ratings (T_A=25°C, Unless Otherwise Noted)

Symbol	Parameter		Rating	Units
V_{DS}	Drain-Source Voltage		100	V
V_{GS}	Gate-Source Voltage		±20	
I_S	Diode Continuous Forward Current	T_C=25°C	15	A
I_D	Continuous Drain Current	T_C=25°C	15	
		T_C=100°C	9.4	
I_{DM} [2]	Pulse Drain Current	T_C=25°C	45	
P_D	Maximum Power Dissipation	T_C=25°C	23	W
		T_C=100°C	9	
$R_{\theta JA}$ [4]	Thermal Resistance-Junction to Ambient	Steady State	95	°C/W
$R_{\theta JC}$	Thermal Resistance-Junction to Case		5.5	
I_{AS} [3]	Avalanche Current, Single pulse	L=0.5mH	8	A
E_{AS} [3]	Avalanche Energy, Single pulse	L=0.5mH	16	mJ
T_{STG}	Storage Temperature Range		-55 to 150	°C
T_J	Maximum Junction Temperature		150	

Electrical Characteristics (T_A=25°C, Unless Otherwise Noted)

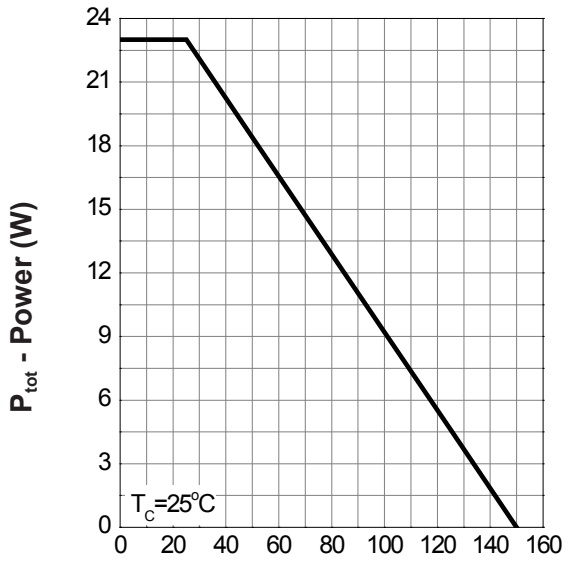
Symbol	Parameter	Conditions	Min.	Typ.	Max.	Units
Static Characteristics						
BV_{DSS}	Drain-Source Breakdown Voltage	V_{GS}=0V , I_D=250μA	100	---	---	V
I_{DSS}	Zero Gate Voltage Drain Current	V_{DS}=80V , V_{GS}=0V	---	---	1.0	μA
		T_J=85°C	---	---	30	
$V_{GS(th)}$	Gate Threshold Voltage	V_{GS}=V_{DS} , I_{DS}=250μA	1.0	1.7	2.5	V
I_{GSS}	Gate Leakage Current	V_{GS}=±20V , V_{DS}=0V	---	---	±100	nA
$R_{DS(ON)}$ [5]	Drain-Source On-state Resistance	V_{GS}=10V , I_D=7A	---	70	82	mΩ
		V_{GS}=4.5V , I_D=4A	---	85	107	
Diode Characteristics						
V_{SD} [5]	Diode Forward Voltage	I_{SD}=7A , V_{GS}=0V	---	0.8	1.3	V
t_{rr}	Reverse Recovery Time	I_{DS}=7A , di_{SD}/dt=100A/μs	---	30	---	ns
Q_{rr}	Reverse Recovery Charge		---	40	---	nC
Dynamic Characteristics [6]						
R_g	Gate Resistance	V_{GS}=0V , V_{DS}=0V , f=1.0MHz	---	1.5	---	Ω
C_{iss}	Input Capacitance	V_{GS}=0V , V_{DS}=50V , Frequency=1.0MHz	---	390	510	pF
C_{oss}	Output Capacitance		---	72	---	
C_{rss}	Reverse Transfer Capacitance		---	20	---	
$T_{d(on)}$	Turn-on Delay Time	V_{DD}=30V , R_L=30Ω , I_{DS}=1A , V_{GEN}=10V , R_G=6Ω	---	8	13	ns
T_r	Turn-on Rise Time		---	6	10	
$T_{d(off)}$	Turn-off Delay Time		---	13	21	
T_f	Turn-off Fall Time		---	11	18	
Gate Charge Characteristics [6]						
Q_g	Total Gate Charge	V_{DS}=50V , V_{GS}=10V , I_{DS}=7A	---	7.5	11	nC
Q_{gs}	Gate-Source Charge		---	2.4	---	
Q_{gd}	Gate-Drain Charge		---	1.6	---	

Note:

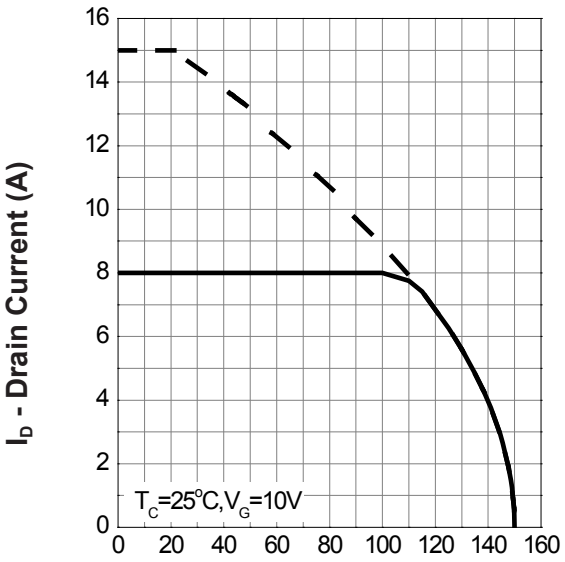
1. Calculated continuous current based on maximum allowable junction temperature. Bonding wire limitation current is 8A.
2. Pulse width limited by max. junction temperature.
3. UIS tested and pulse width limited by maximum junction temperature 150°C (initial temperature T_J=25°C).
4. Surface Mounted on 1in^2 pad area.
5. Pulse test ; pulse width≤300μs, duty cycle≤2%.
6. Guaranteed by design, not subject to production testing.

Typical Characteristics

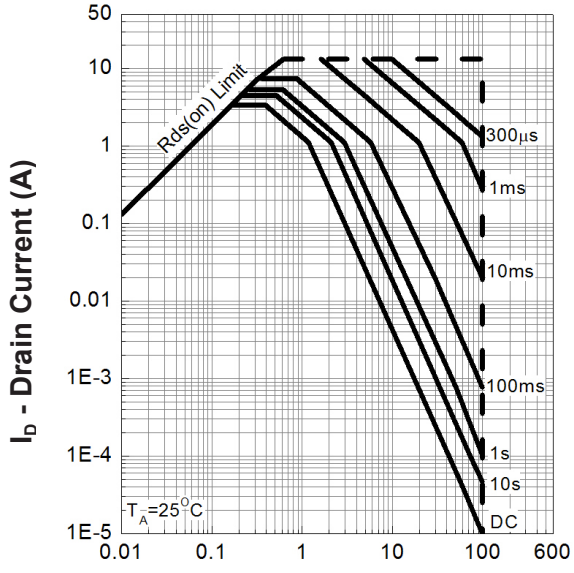
Power Dissipation



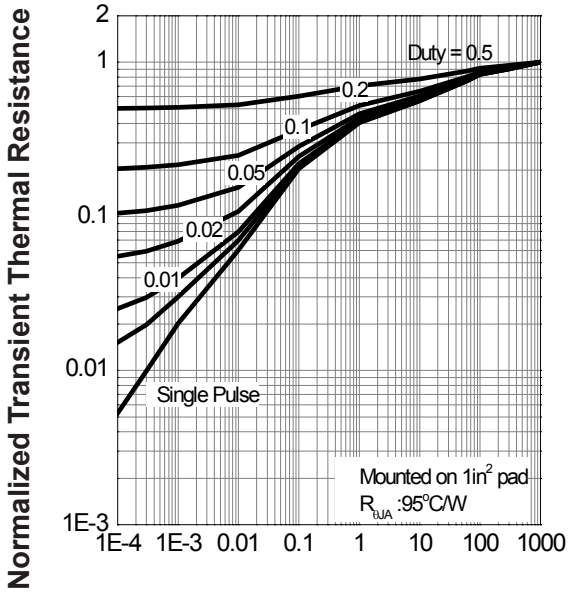
Drain Current



Safe Operation Area

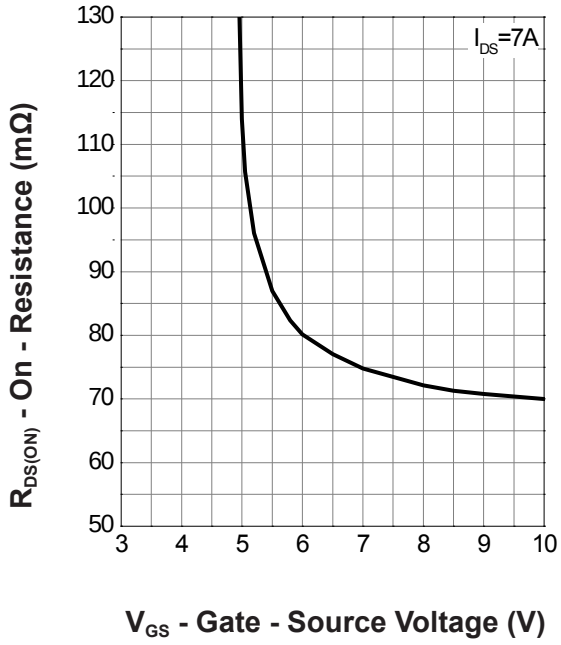


Thermal Transient Impedance

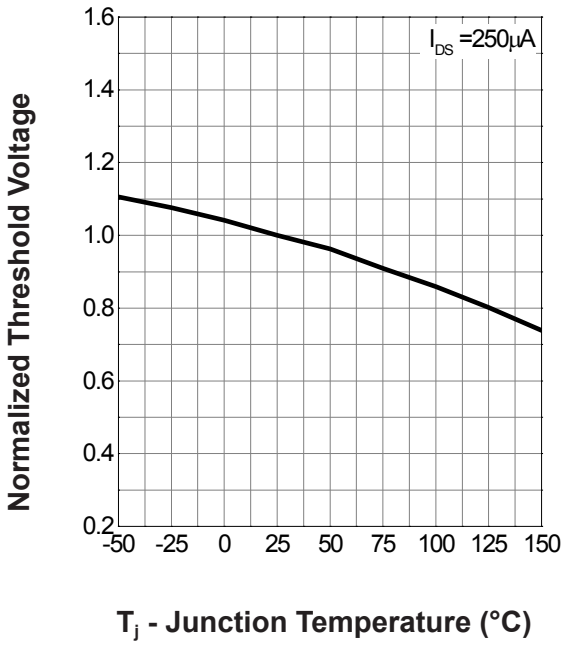


Typical Characteristics (Cont.)

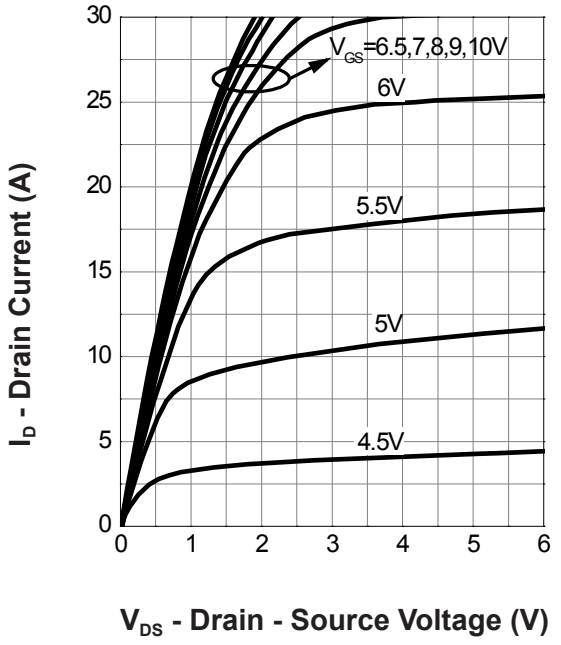
Gate-Source On Resistance



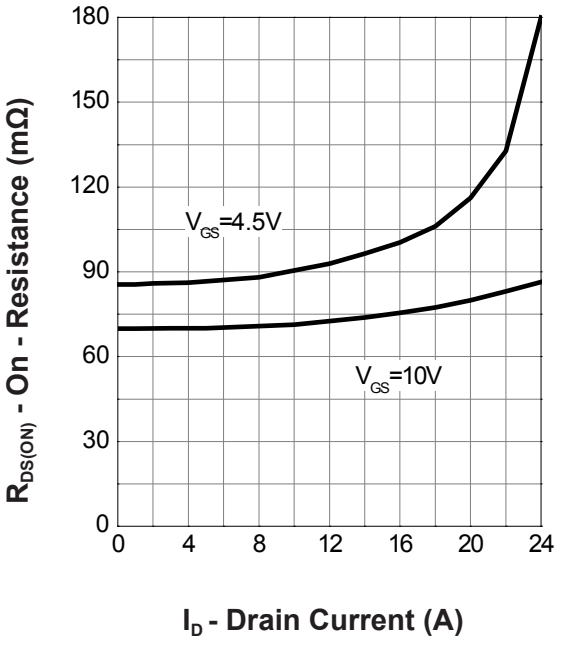
Gate Threshold Voltage



Output Characteristics

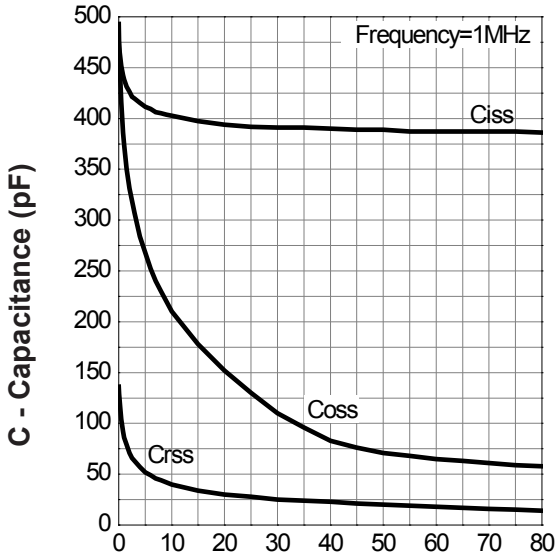


Drain-Source On Resistance

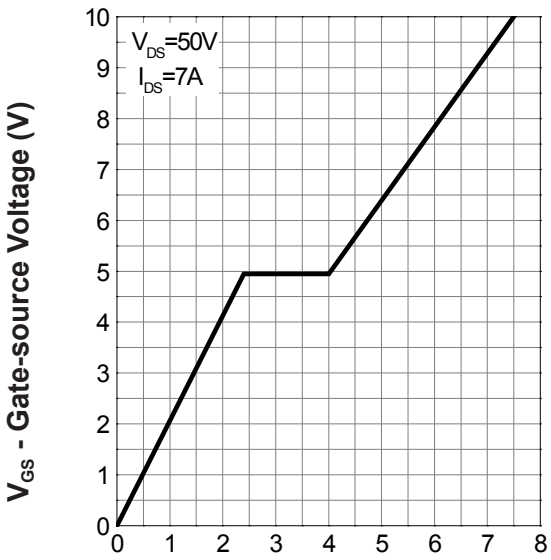


Typical Characteristics (Cont.)

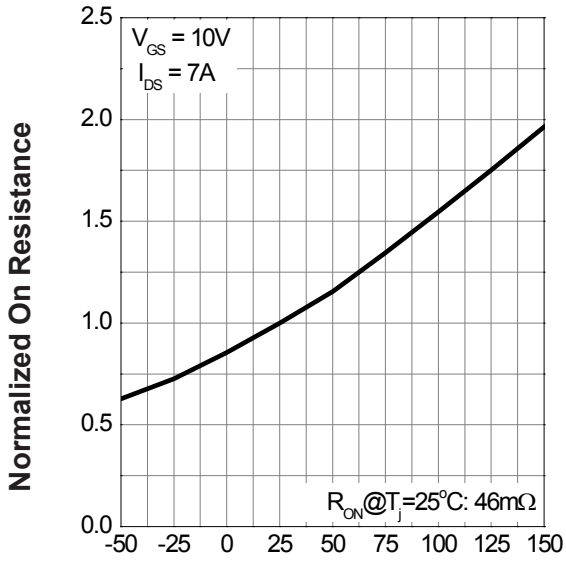
Capacitance



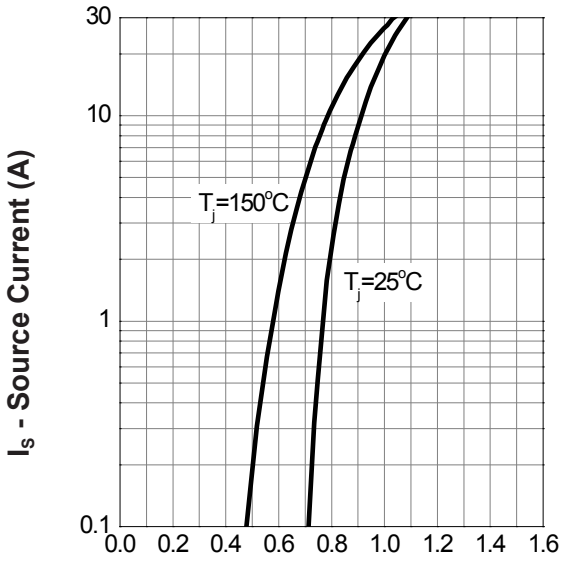
Gate Charge



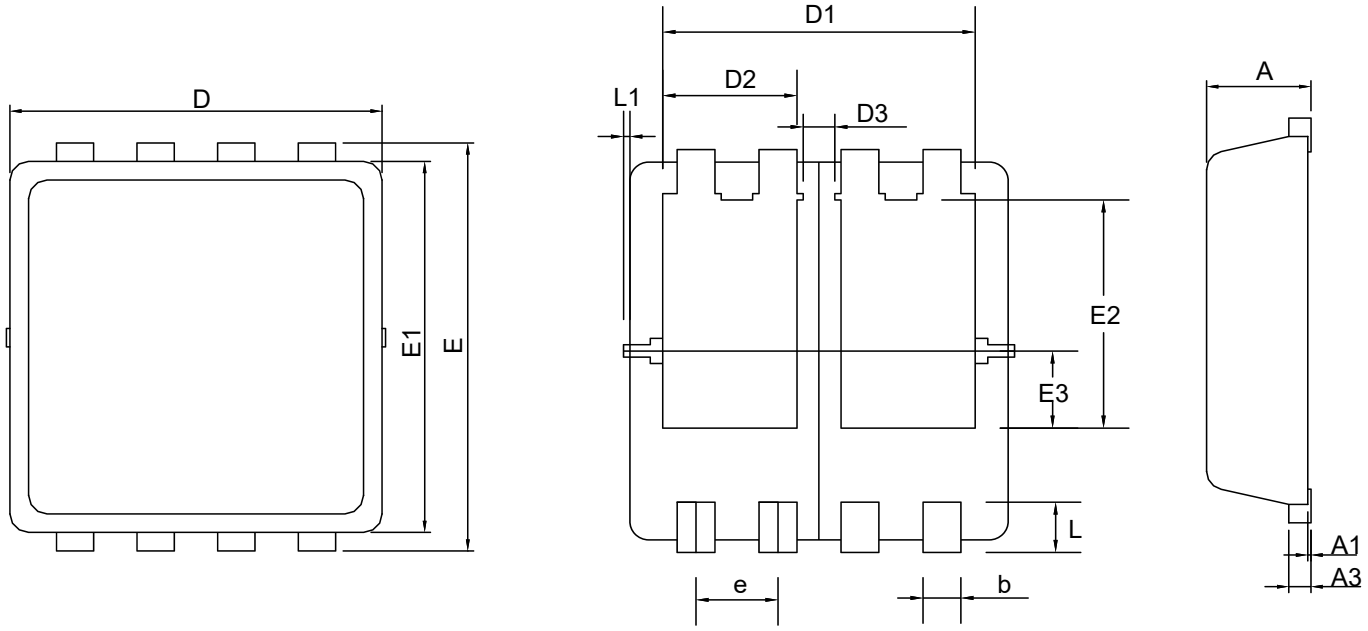
Drain-Source On Resistance



Source-Drain Diode Forward

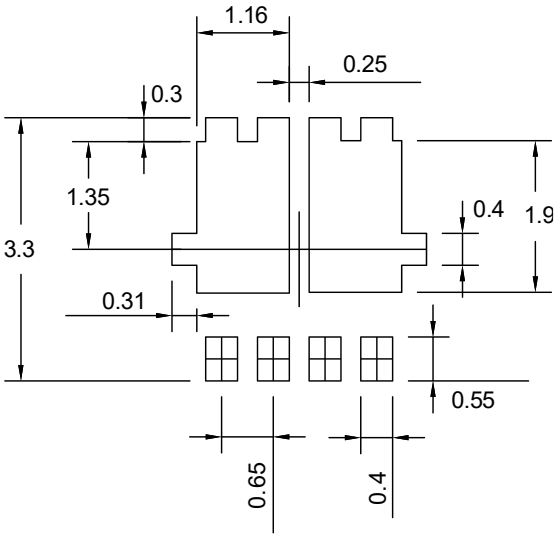


Packaging information



SYMBOL	DFN3X3-8L			
	MILLIMETERS		INCHES	
	MIN.	MAX.	MIN.	MAX.
A	0.70	0.90	0.028	0.035
A1	0.00	0.05	0.000	0.002
A3	0.10	0.25	0.004	0.010
b	0.24	0.35	0.009	0.014
D	2.90	3.10	0.114	0.122
D1	2.375	2.575	0.094	0.101
D2	0.963	1.163	0.038	0.046
D3	0.175	0.275	0.007	0.011
E	3.10	3.30	0.122	0.130
E1	2.90	3.10	0.114	0.122
E2	1.713	1.913	0.067	0.075
E3	0.425	0.625	0.017	0.025
e	0.65 BSC		0.026 BSC	
L	0.30	0.50	0.012	0.020
L1	0.000	0.100	0.000	0.004

RECOMMENDED LAND PATTERN



UNIT: mm

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